Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- Exposed drain pad for excellent thermal conduction

3. Applications

- · Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	13.5	Α
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 9.5 \text{ A}; T_j = 25 \text{ °C}$		-	11	13	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15776	D
2	D	drain		
3	G	gate	2 5	G—(III)
4	S	source	3 8 4	mbb076 S
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PMPB10XN		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB10XN	5C

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	13.5	А
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	9.5	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	6	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	38	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.9	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		•			
I _S	source current	T _{amb} = 25 °C	[1]	-	1.9	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

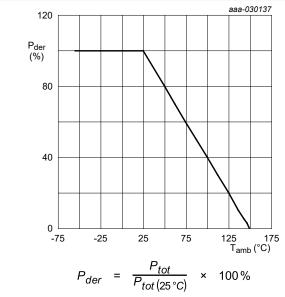


Fig. 1. Normalized total power dissipation as a function of ambient temperature

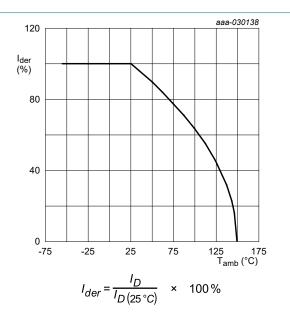


Fig. 2. Normalized continous drain current as a function of ambient temperature

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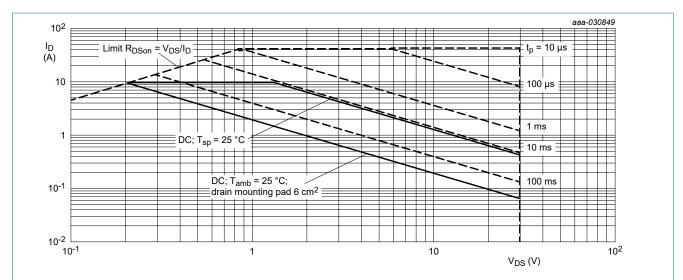


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

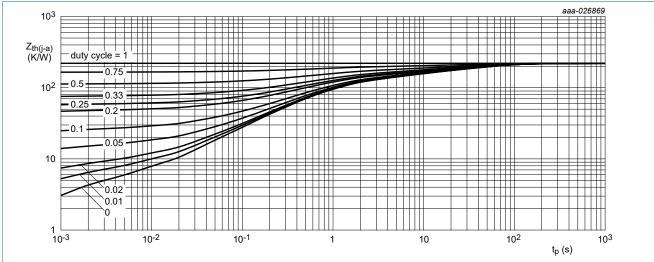
30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

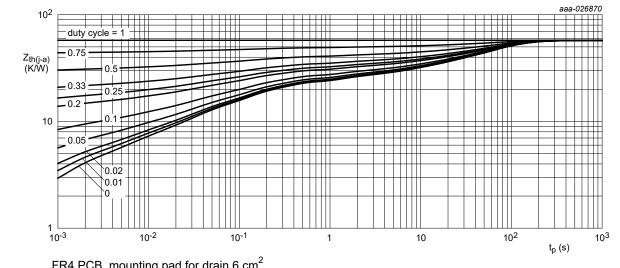
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		[1]	-	223	256	K/W	
	junction to ambient		[2]	-	57	66	K/W
		in free air; t ≤ 5 s	[2]	-	29	33	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	6	10	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



FR4 PCB, mounting pad for drain 6 cm²

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 9.5 A; T _j = 25 °C	-	11	13	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 9.5 A; T _j = 150 °C	-	18	22	mΩ
		V_{GS} = 2.5 V; I_D = 8.4 A; T_j = 25 °C	-	13	16	mΩ
		V _{GS} = 1.8 V; I _D = 3 A; T _j = 25 °C	-	19	28	mΩ
		$V_{GS} = 1.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	35	90	mΩ
9fs	forward transconductance	V _{DS} = 10 V; I _D = 9.5 A; T _j = 25 °C	-	18.4	-	S
R_G	gate resistance	f = 1 MHz	-	2.4	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 9.5 A; V _{GS} = 4.5 V;	-	20	30	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	3	-	nC
Q _{GD}	gate-drain charge		-	6	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	1761	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	137	-	pF
C _{rss}	reverse transfer capacitance		-	119	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 9.5 A; V _{GS} = 4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	11	-	ns
t _{d(off)}	turn-off delay time	1	-	33	-	ns
t _f	fall time	1	-	14	-	ns
Source-dra	in diode	•		1		1
V_{SD}	source-drain voltage	I _S = 1.9 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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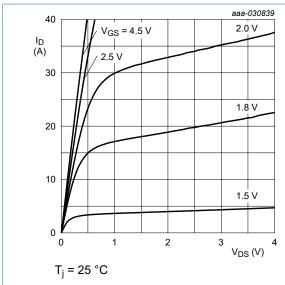


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

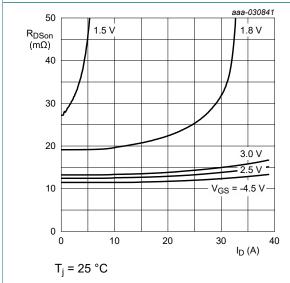


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

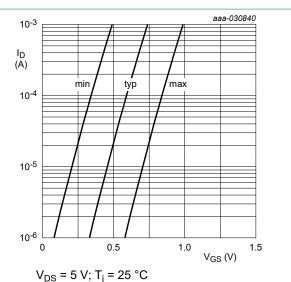


Fig. 7. Sub-threshold drain current as a function of

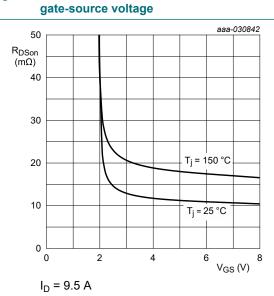


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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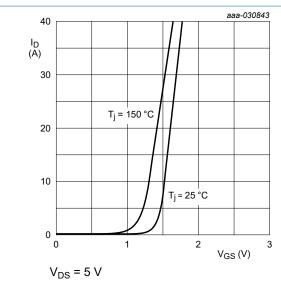


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

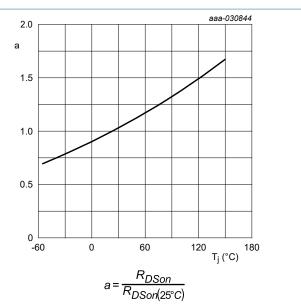


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

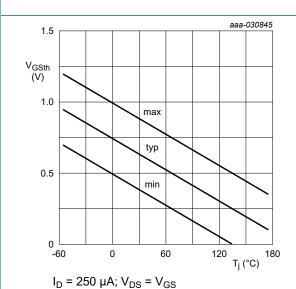
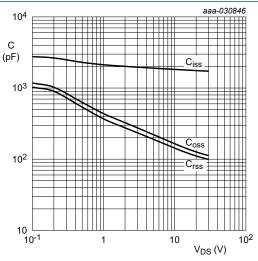


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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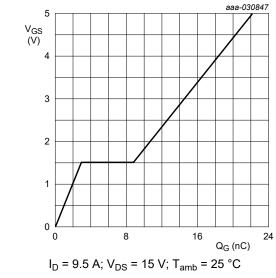


Fig. 15. Gate charge waveform definitions

Q_{GS2}

Q_{GS}

-Q_{GD}· Q_{G(tot)}-

aaa-030347

V_{GS(pl)}

V_{GS(th)}

 V_{GS}

Q_{GS1}



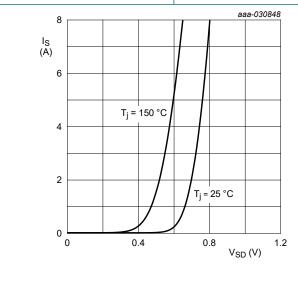
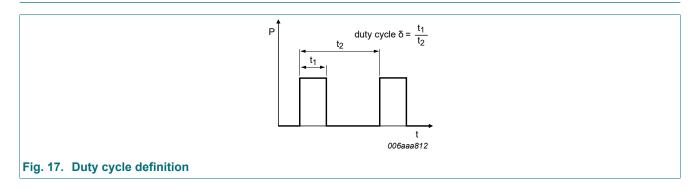


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

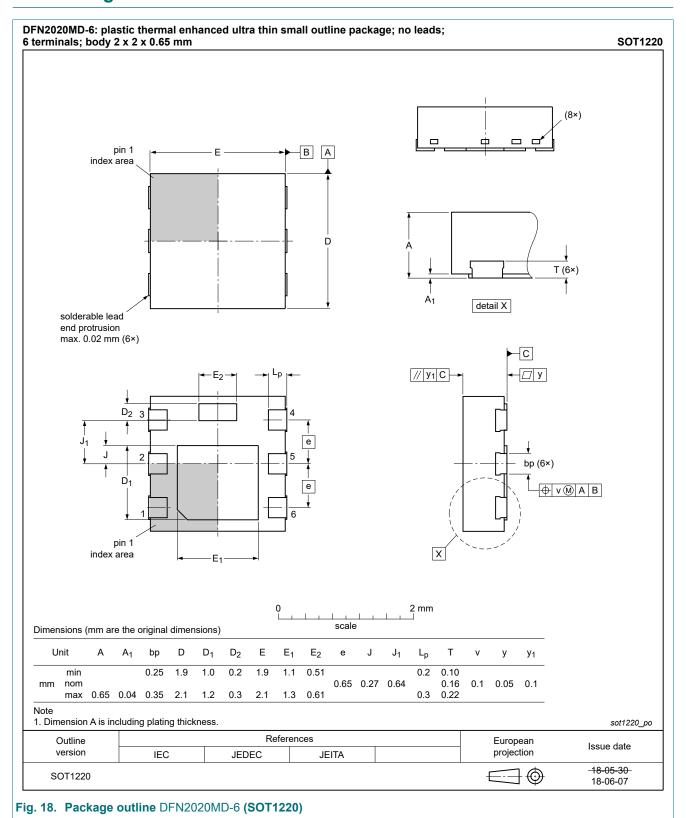
 $V_{GS} = 0 V$



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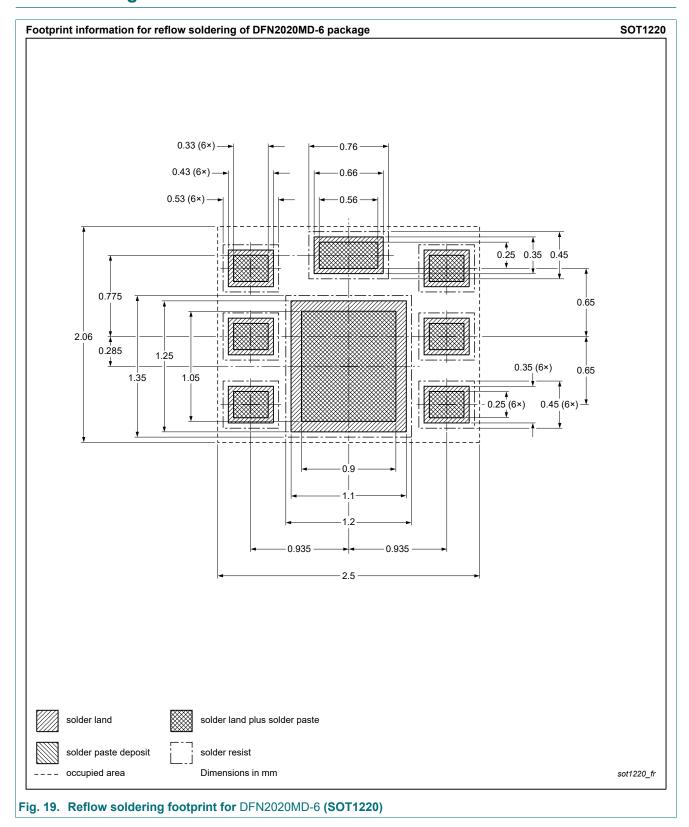
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB10XN v.1	20200311	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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